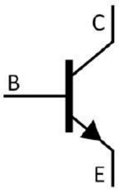
/ Descriptions

SOT-23	NPN	Silicon NPN transistor in a SOT-23 Plastic Package.

/ F

Low current, Low voltage,HF Product.

General purpose amplifier and switching.



PIN 1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Range	100～300
Marking	• H1A

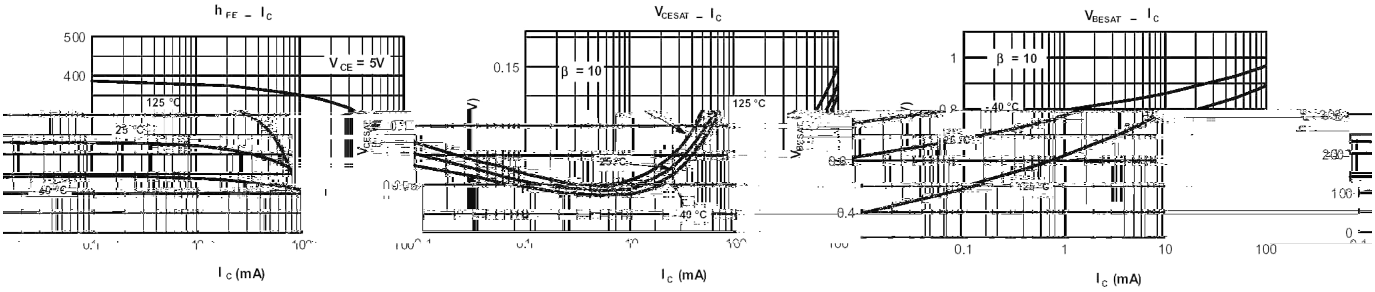
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Collector Power Dissipation	*P_C	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

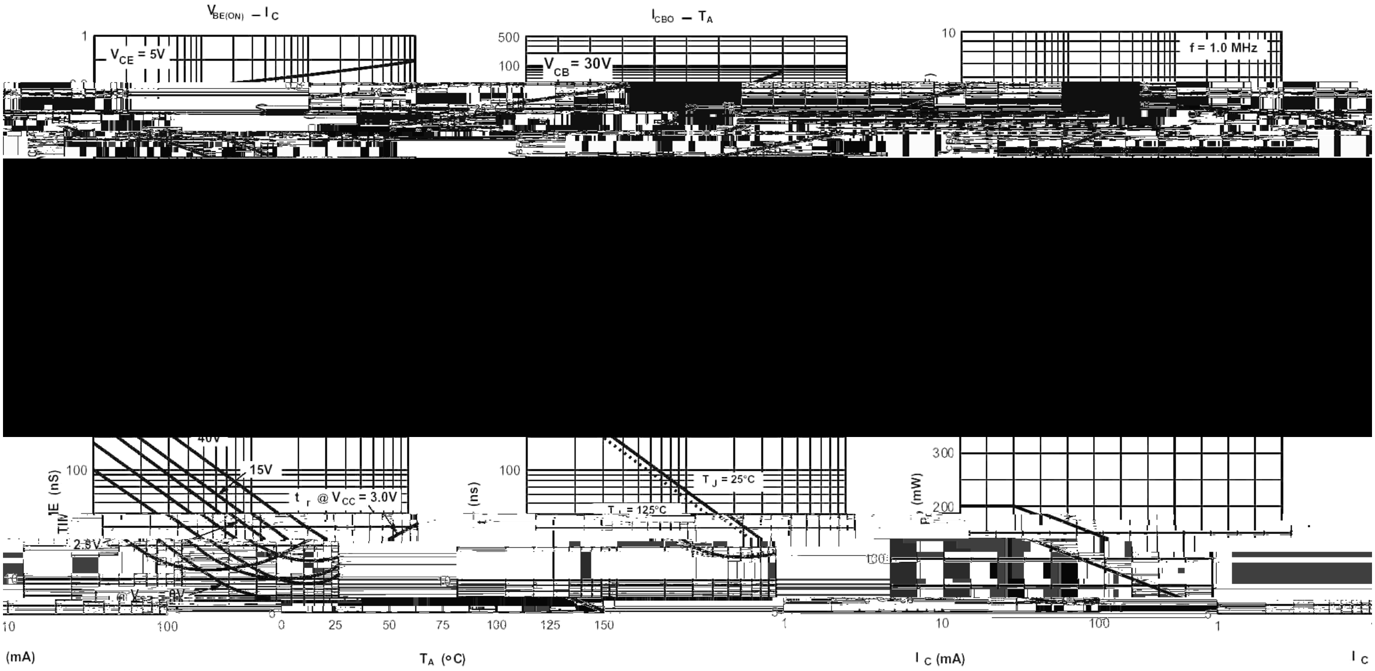
* 7×5×0.6mm *When mounted on a 7×5×0.6mm ceramic board

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

Collector to Base Breakdo

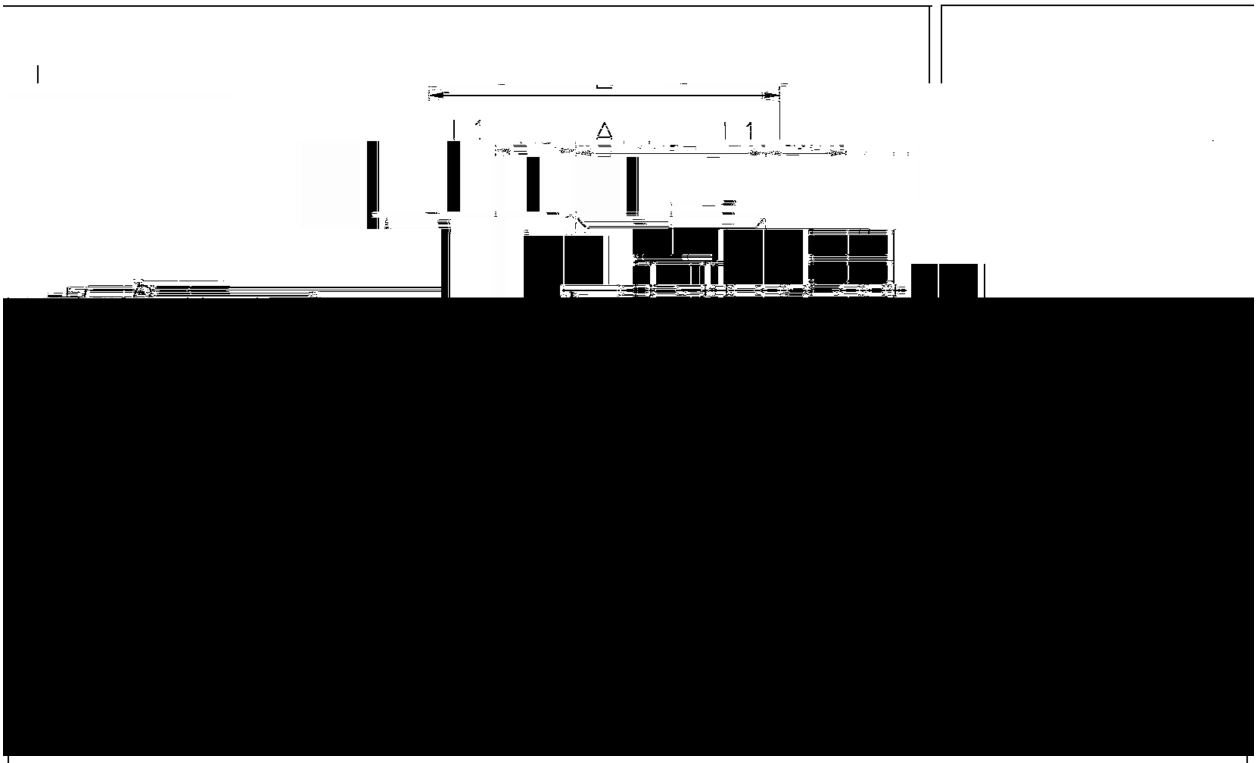
/ Electrical Characteristic Curve





[redacted]

/ Package Dimensions

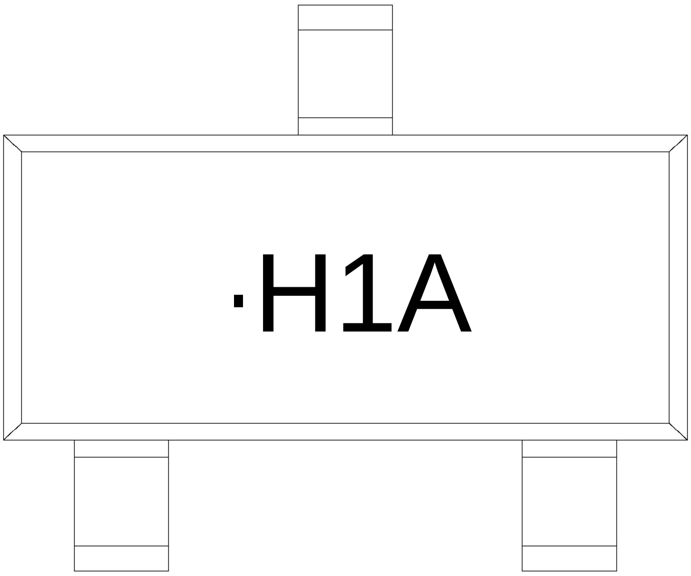


Symbol	Dimensions In Millimeters Min	Max
[illegible]	0.05	0.20
K	0	0.10
M	0.20MIN	
P	7°	

1.20 0.45 0.65 0.91

Symbol	Dimensions In Millimeters Min	Max
A	1.05	1.50
B	2.70	3.10
E	1.70	2.10
E1	0.85	1.05
b	0.35	0.55

/ Marking Instructions



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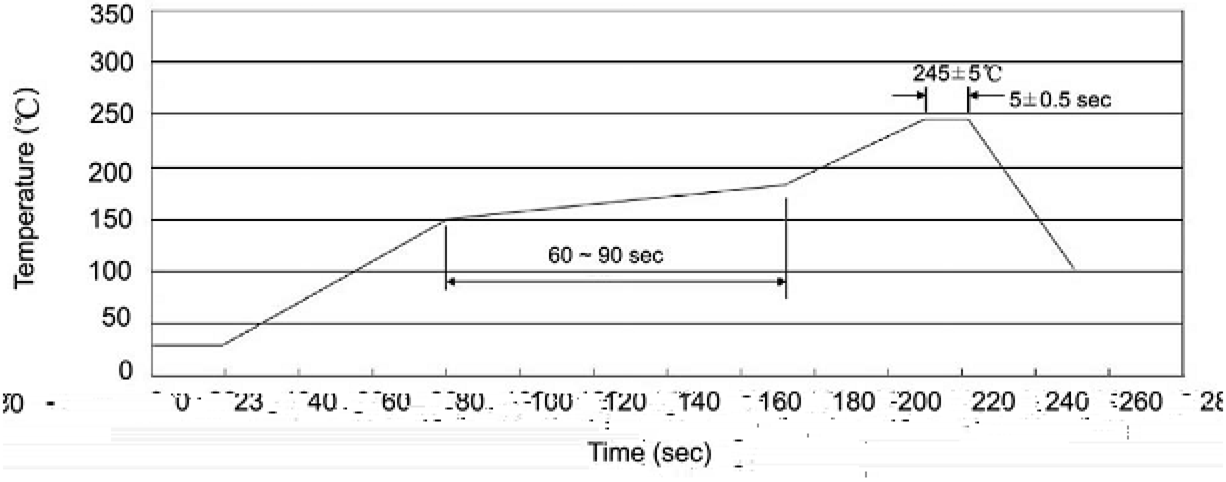
H

1A

Note:

·	Identify
H	Company Code
1A	Product Type Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

1、预热温度 25～150℃，时间 60～90sec;

2、峰值温度 245±5℃，时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2～10℃/sec.

Note:

1.Preheating:25~150℃, Time:60~90sec.

2.Peak Temp.:245±5℃, Duration:5±0.5sec.

3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度：260±5℃　　时间：10±1 sec.　　Temp.:260±5℃　　Time:10±1 sec

/ Packaging SPEC.

卷盘包

Package Type